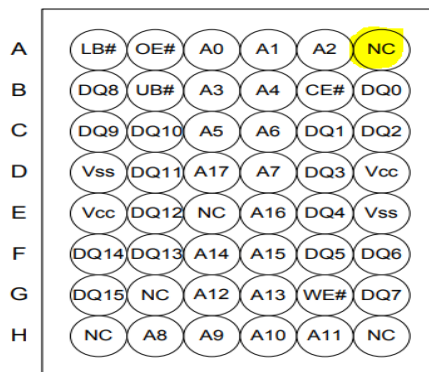


AS6C4016A-55BIN vs AS6C4016B-45BIN vs AS6CE4016B-45BIN Comparison

Part Number & result Parameter	AS6C4016A-55BIN	AS6C4016B-45BIN	AS6CE4016B-45BIN
Product Description	Low Power ASRAM	Low Power ASRAM	Low Power ASRAM with ECC
Capacity	4Mb	4Mb	4Mb
Memory Organization	256K x 16bits	256K x 16bits	256K x 16bits
Operating Power Supply	V _{CC} = 2.7V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)
I/O Capacitance	CIO: 10pf (max.)	CIO: 8pf(max.)	CIO: 8pf(max.)
Read Cycle Time (t _{RC})	55ns (min.)	45ns (min.)	45ns (min.)
Write Cycle Time (t _{WC})	55ns (min.)	45ns (min.)	45ns (min.)
Addr Access Time(t _{AA})	55ns (max.)	45ns (max.)	45ns (max.)
OE Access Time (t _{OE})	30ns (max.)	25ns (max.)	25ns (max.)
V _{OH} (V) @ -1.0mA	2.4 (min.)	2.2 (min.)	2.2 (min.)
V _{OL} (V) @ 2mA	0.6 (max.)	0.4 (max.)	0.4 (max.)
V _{IH} (V)	2.2 (min.)	2.2 (min.)	2.2 (min.)
V _{IL} (V)	0.6 (max.)	0.6 (max.)	0.6 (max.)
I _{LI} / I _{LO} (uA)	1 (max.)	1 (max.)	1 (max.)
I _{CC} (Cycle Time=Min) Operating Current	35mA (max.)	20mA (max.)	20mA (max.)
I _{CC1} (Cycle Time=1uS) Operating Current	3mA (max.)	4mA (max.)	5mA (max.)
I _{sb1} (Standby Current)	0.25uA (Typ) @ 3.3V/25C 4uA (max.) @ 3.6V	2uA (Typ) @ 3.3V/25C 12uA (max.)	2.5uA (Typ) @ 3.3V/25C 20uA (max.)
V _{DR}	1.5V	1.5V	1.5V
Package	6mm x 7mm FBGA	6mm x 8mm BGA	6mm x 8mm BGA
Package Material	Pb and Halogen Free	Pb and Halogen Free	Pb and Halogen Free
Pin to Pin Compatible	Yes, Single Chip Enable		
	 TFBGA(See through with Top View)		



12815 NE 124th St STE#D, Kirkland, WA-98034
